

Chen Shang

List of Publications by Year in descending order

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docs citations

24
times ranked

549
citing authors

#	ARTICLE	IF	CITATIONS
1	High efficiency low threshold current 1.3 μm InAs quantum dot lasers on on-axis (001) GaP/Si. Applied Physics Letters, 2017, 111, .	1.5	114
2	A Review of High-Performance Quantum Dot Lasers on Silicon. IEEE Journal of Quantum Electronics, 2019, 55, 1-11.	1.0	107
3	High-temperature reliable quantum-dot lasers on Si with misfit and threading dislocation filters. Optica, 2021, 8, 749.	4.8	76
4	Perspectives on Advances in Quantum Dot Lasers and Integration with Si Photonic Integrated Circuits. ACS Photonics, 2021, 8, 2555-2566.	3.2	67
5	Directly modulated quantum dot lasers on silicon with a milliamper threshold and high temperature stability. Photonics Research, 2018, 6, 776.	3.4	55
6	O-band electrically injected quantum dot micro-ring lasers on on-axis (001) GaP/Si and V-groove Si. Optics Express, 2017, 25, 26853.	1.7	53
7	Low Dark Current High Gain InAs Quantum Dot Avalanche Photodiodes Monolithically Grown on Si. ACS Photonics, 2020, 7, 528-533.	3.2	49
8	Tunable quantum dot lasers grown directly on silicon. Optica, 2019, 6, 1394.	4.8	49
9	A Pathway to Thin GaAs Virtual Substrate on On-axis Si (001) with Ultralow Threading Dislocation Density. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000402.	0.8	48
10	1.3 μm Quantum Dot Distributed Feedback Lasers Directly Grown on (001) Si. Laser and Photonics Reviews, 2020, 14, 2000037.	4.4	40
11	Defect filtering for thermal expansion induced dislocations in III ν lasers on silicon. Applied Physics Letters, 2020, 117, .	1.5	38
12	Low Threshold Quantum Dot Lasers Directly Grown on Unpatterned Quasi-Nominal (001) Si. IEEE Journal of Selected Topics in Quantum Electronics, 2020, 26, 1-9.	1.9	29
13	Directly Modulated Single-Mode Tunable Quantum Dot Lasers at 1.3 μm . Laser and Photonics Reviews, 2020, 14, 1900348.	4.4	24
14	Low-Threshold Epitaxially Grown 1.3 μm InAs Quantum Dot Lasers on Patterned (001) Si. IEEE Journal of Selected Topics in Quantum Electronics, 2019, 25, 1-7.	1.9	23
15	Reduced dislocation growth leads to long lifetime InAs quantum dot lasers on silicon at high temperatures. Applied Physics Letters, 2021, 118, .	1.5	20
16	Low Dark Current 1.55 Micrometer InAs Quantum Dash Waveguide Photodiodes. ACS Nano, 2020, 14, 3519-3527.	7.3	16
17	Kinetically limited misfit dislocations formed during post-growth cooling in III ν lasers on silicon. Journal Physics D: Applied Physics, 2021, 54, 494001.	1.3	7
18	Monolithic Passive-Active Integration of Epitaxially Grown Quantum Dot Lasers on Silicon. Physica Status Solidi (A) Applications and Materials Science, 2022, 219, 2100522.	0.8	7

#	ARTICLE	IF	CITATIONS
19	A Review of the Reliability of Integrated IR Laser Diodes for Silicon Photonics. Electronics (Switzerland), 2021, 10, 2734.	1.8	6
20	Crack propagation in low dislocation density quantum dot lasers epitaxially grown on Si. APL Materials, 2022, 10, .	2.2	6
21	Quantum Hall effect of the topological insulator state of cadmium arsenide in Corbino geometry. Applied Physics Letters, 2021, 118, 261901.	1.5	1
22	GaAs epitaxy on (001) Si: below 1Å — 10^6 cm^{-2} dislocation density with 2.4 μm buffer thickness. , 2020, , .		0
23	1.3 μm High Performance Regrown Distributed Feedback Lasers Epitaxially Grown on Si. , 2021, , .		0